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IN THE CLAIMS

Please amend the claims as follows. All pending claims are rewritten below in clean form pursuant to Rule 1.121(4)(c). Claims 1-20 are cancelled and new claims 21-29 are added. Since all pending claims are now new claims, a marked up version is not provided.

Cancel claims 1-20 without prejudice to their subject matter.

Add new claims as follows.

21. (New) A method of making a semiconductor device comprising:

providing a substrate having a surface and a diffused region of a second conductivity type for forming a channel of the semiconductor device;

forming a drain of a first conductivity type at the surface for electrically coupling a drain electrode to the channel;

growing an oxide less than one-thousand angstroms thick over the drain; and

introducing dopants of a second conductivity type through the oxide between the channel and the drain electrode to form a first charge balancing layer within the drain and at the surface.

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22. (New) The method of claim 21, wherein the step of forming a drain further comprises:

forming a first area of first dopant concentration by performing a first area implant; and

forming a second area of second dopant concentration different than the first dopant concentration by performing a second area implant, the second area implant is laterally offset from the first area.

23. (New) The method of claim 21, further comprising introducing dopants of the second conductivity type through the oxide to form a second charge balancing layer within the drain and under the first charge balancing layer.

24. (New) The method of claim 23, further comprising forming a gate region overlying the oxide.

25. (New) The method of claim 21, further comprising forming a diffused region of the first conductivity type.

26. (New) The method of claim 25, further comprising forming a source diffusion region in the diffused region of the first conductivity type.

27. (New) The method of claim 21, further comprising forming a drain diffusion region at the surface of the drain.

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28. (New) The method of claim 21, wherein introducing dopants includes the step of:

disposing a first island of dielectric material at a top of the substrate within the drain; and

disposing a second island of dielectric material at a top of the substrate within the drain and laterally

separated from the first island of dielectric material; and

masking the dopants with the first and second islands to form the first charge balancing layer between the first and second islands of dielectric material.

29. (New) The method of claim 28, wherein the first and second islands of dielectric material are formed to a thickness of greater than one micrometer.
